MOSFETs Silicon N-channel MOS (U-MOSⅧ-H)

# TPN1110ENH

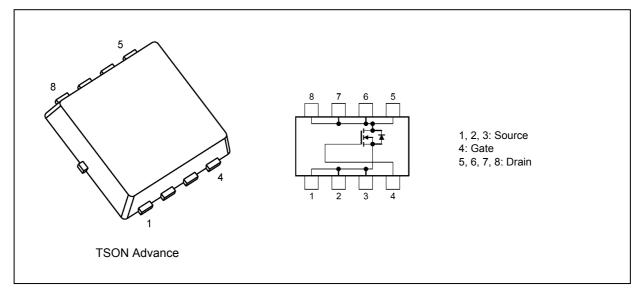
#### 1. Applications

- High-Efficiency DC-DC Converters
- Switching Voltage Regulators

#### 2. Features

- (1) High-speed switching
- (2) Small gate charge:  $Q_{SW} = 2.6 \text{ nC}$  (typ.)
- (3) Low drain-source on-resistance:  $R_{DS(ON)} = 96 \text{ m}\Omega \text{ (typ.)} (V_{GS} = 10 \text{ V})$
- (4) Low leakage current:  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 200 \ V)$
- (5) Enhancement mode:  $V_{th}$  = 2.0 to 4.0 V (V\_{DS} = 10 V,  $I_{D}$  = 0.2 mA)

#### 3. Packaging and Internal Circuit



#### 4. Absolute Maximum Ratings (Note) ( $T_a = 25$ °C unless otherwise specified)

Characterist	ics		Symbol	Rating	Unit
Drain-source voltage			V <sub>DSS</sub>	200	V
Gate-source voltage			V <sub>GSS</sub>	±20	
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	Ι <sub>D</sub>	13	A
Drain current (DC)	(Continuous)	(Note 1)	Ι <sub>D</sub>	7.2	
Drain current (pulsed)	(t = 1 ms)	(Note 1)	I <sub>DP</sub>	25	
Power dissipation	(T <sub>c</sub> = 25 °C)		PD	39	W
Power dissipation	(t = 10 s)	(Note 3)	PD	1.9	
Power dissipation	(t = 10 s)	(Note 4)	PD	0.7	
Single-pulse avalanche energy		(Note 5)	E <sub>AS</sub>	33	mJ
Avalanche current			I <sub>AR</sub>	7.2	A
Channel temperature			T <sub>ch</sub>	150	°C
Storage temperature			T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics			Symbol	Max	Unit
Channel-to-case thermal resistance	(T <sub>c</sub> = 25 °C)		R <sub>th(ch-c)</sub>	3.20	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 3)	R <sub>th(ch-a)</sub>	65.7	
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 4)	R <sub>th(ch-a)</sub>	178	

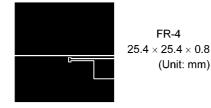
Note 1: Ensure that the channel temperature does not exceed 150 °C.

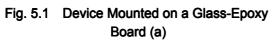
Note 2: Limited by silicon chip capability.

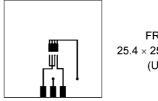
Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V\_DD = 60 V, T\_ch = 25 °C (initial), L = 1.0 mH, I\_{AR} = 7.2 A







FR-4 25.4 × 25.4 × 0.8 (Unit: mm)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

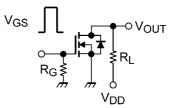
#### 6. Electrical Characteristics

#### 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±20 V, $V_{DS}$ = 0 V	_	_	±0.1	μA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V	_	_	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	200	_	_	V
	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	140	_	_	
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.2 mA	2.0	_	4.0	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3.6 A	_	96	114	mΩ

### 6.2. Dynamic Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	460	600	pF
Reverse transfer capacitance	C <sub>rss</sub>		_	3.0	50	
Output capacitance	C <sub>oss</sub>		_	55	—	
Gate resistance	r <sub>g</sub>	—	_	4.0	6.0	Ω
Switching time (rise time)	t <sub>r</sub>	See Fig. 6.2.1	_	5.2	_	ns
Switching time (turn-on time)	t <sub>on</sub>		_	14	_	
Switching time (fall time)	t <sub>f</sub>			4.5	_	
Switching time (turn-off time)	t <sub>off</sub>		_	19	_	



 $V_{DD} \approx 100 V$   $V_{GS} = 0 V/10 V$   $I_{D} = 3.6 A$   $R_{L} = 27.8 \Omega$   $R_{G} = 4.7 \Omega$   $Duty \le 1 \%, t_{w} = 10 \ \mu s$ 

Fig. 6.2.1 Switching Time Test Circuit

#### 6.3. Gate Charge Characteristics ( $T_a = 25$ °C unless otherwise specified)

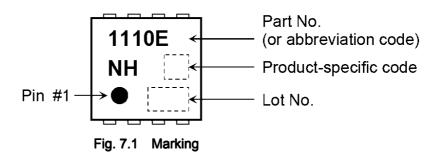
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 100 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 7.2 \text{ A}$	—	7.0	—	nC
Gate-source charge 1	Q <sub>gs1</sub>		_	2.4	_	nC
Gate-drain charge	Q <sub>gd</sub>	]	_	1.5	_	
Gate switch charge	Q <sub>SW</sub>			2.6		

#### 6.4. Source-Drain Characteristics ( $T_a = 25 \ ^{\circ}C$ unless otherwise specified)

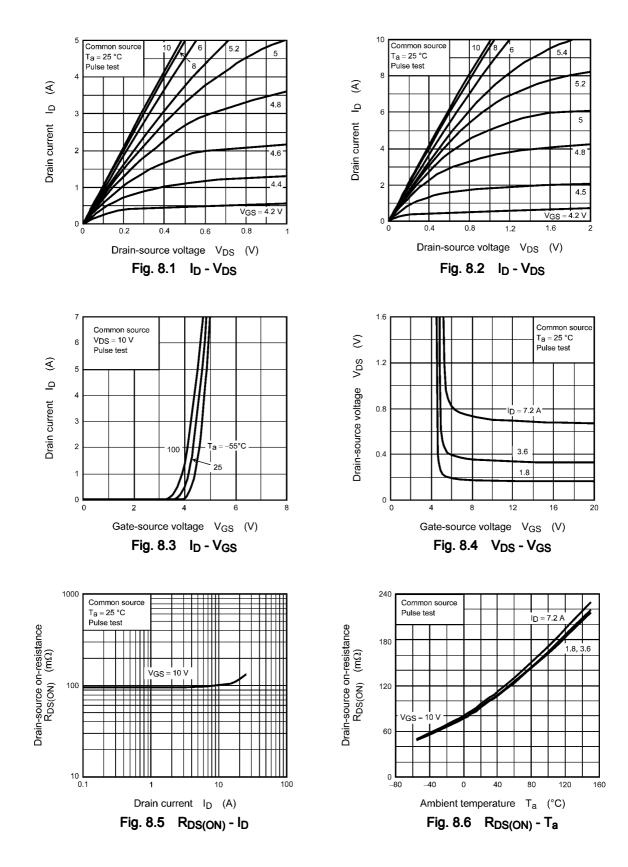
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed)	(Note 6)	I <sub>DRP</sub>	—	_	_	25	А
Diode forward voltage		V <sub>DSF</sub>	I <sub>DR</sub> = 7.2 A, V <sub>GS</sub> = 0 V		_	-1.2	V

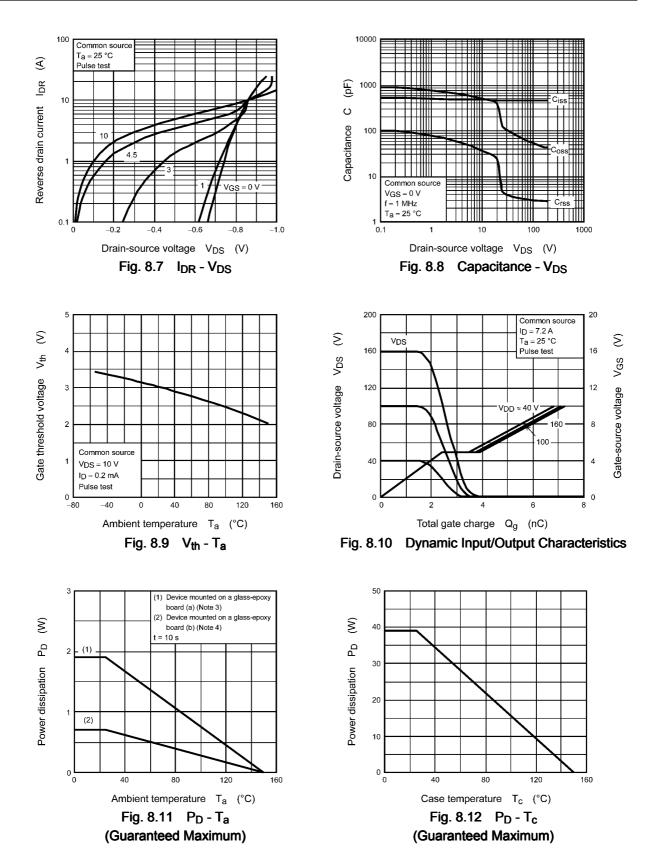
Note 6: Ensure that the channel temperature does not exceed 150 °C.

#### 7. Marking



#### 8. Characteristics Curves (Note)





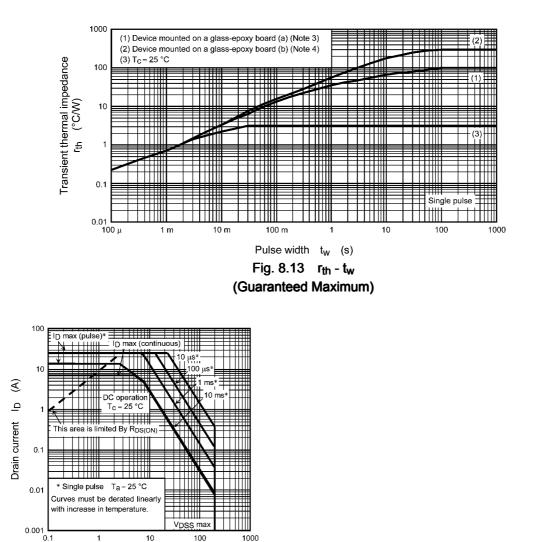


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10

Drain-source voltage VDS (V) Fig. 8.14 Safe Operating Area (Guaranteed Maximum)

100



Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

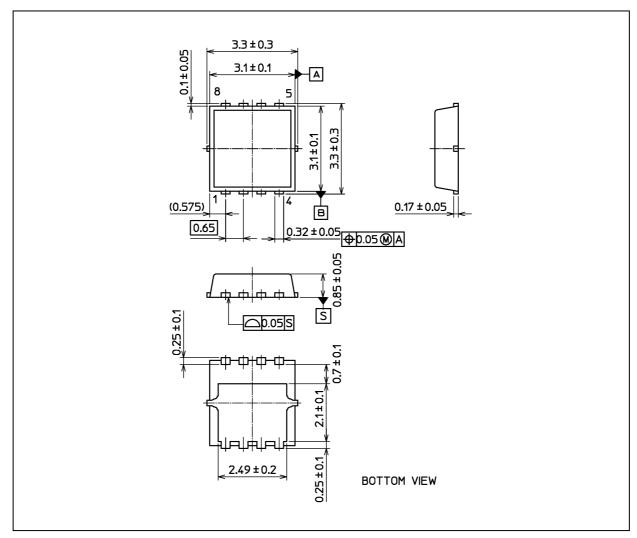
1000



### TPN1110ENH

#### **Package Dimensions**

Unit: mm



Weight: 0.02 g (typ.)

Package Name(s)
TOSHIBA: 2-3X1S
Nickname: TSON Advance

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